

## Abstract of the Disclosure

A method for removing particles on semiconductor wafers, which is a process involving a cleaning tank filled with a first cleaning solution consisting of hydrogen water, is accomplished by carrying out said process in which the in-solution hydrogen concentration in said first cleaning solution is in the range 20% to 50% of its saturated concentration (0.3 ppm to 0.8 ppm), a process in which ultrasonic waves are generated in said first cleaning solution in said cleaning tank, and a first cleaning process in which one or multiple said semiconductor wafers are cleaned for a prescribed time in said cleaning tank. Here the in-solution hydrogen concentration in said first cleaning solution is in the range 0.3 ppm to 0.8 ppm.

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